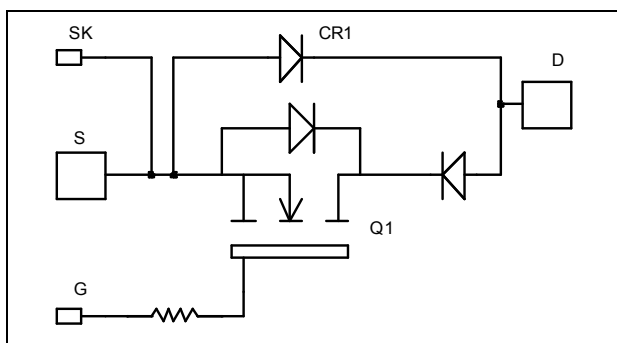


Single switch Series & parallel diodes MOSFET Power Module

$$V_{DSS} = 500V$$

$$R_{DSon} = 13m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 335A \text{ @ } T_c = 25^\circ C$$



Application

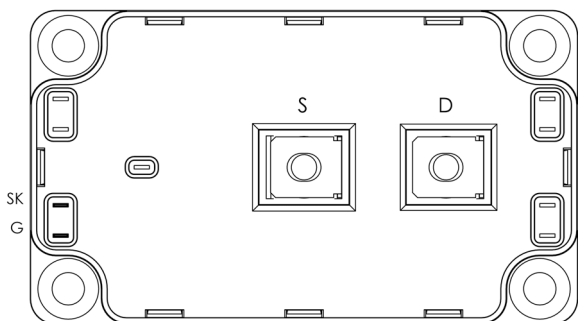
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration
- AlN substrate for improved thermal performance

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant



All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	1340	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	15	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	3290 W
I_{AR}	Avalanche current (repetitive and non repetitive)	71	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			400	μA
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 167.5A$		13	15	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 20mA$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 300	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		42.2		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		8.24		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		0.42		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 250V$ $I_D = 335A$		800		nC
Q_{gs}	Gate – Source Charge			200		
Q_{gd}	Gate – Drain Charge			420		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 335A$ $R_G = 0.8\Omega$		21		ns
T_r	Rise Time			42		
$T_{d(off)}$	Turn-off Delay Time			96		
T_f	Fall Time			100		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 335A, R_G = 0.8\Omega$		4		mJ
E_{off}	Turn-off Switching Energy			4.16		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 335A, R_G = 0.8\Omega$		6.32		mJ
E_{off}	Turn-off Switching Energy			4.64		
R_{thJC}	Junction to Case Thermal Resistance				0.038	°C/W

Series diode ratings and characteristics

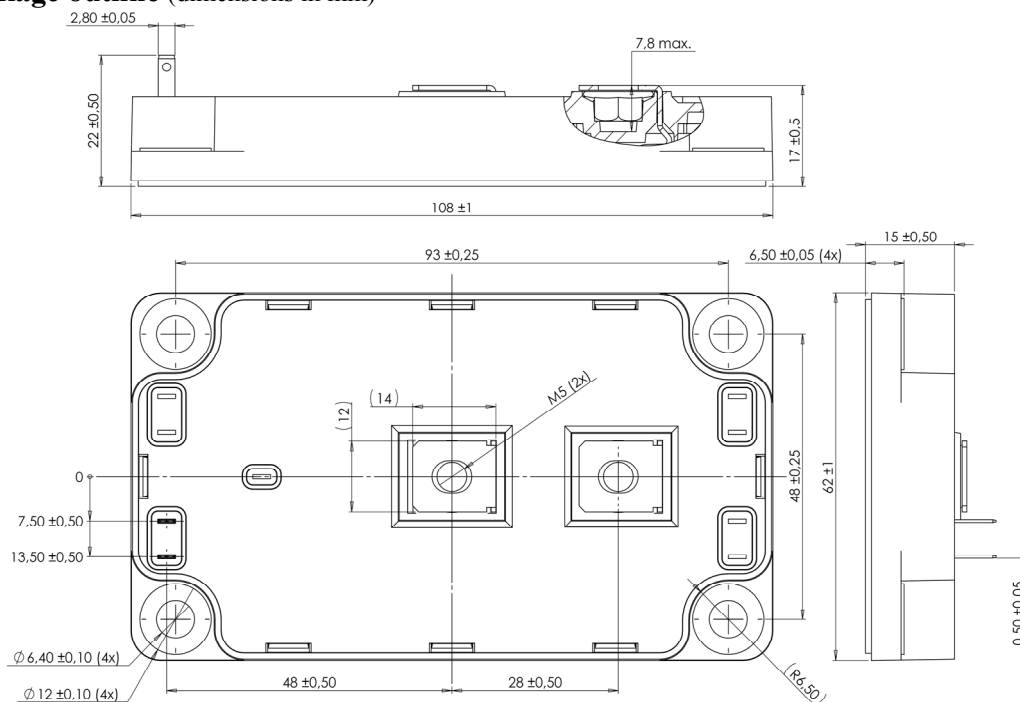
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V				150	μA
I _F	DC Forward Current		T _c = 80°C		360		A
V _F	Diode Forward Voltage	I _F = 360A			1.7	2.5	V
		I _F = 720A			2		
		I _F = 360A	T _j = 125°C		1.4		
t _{rr}	Reverse Recovery Time	I _F = 360A V _R = 400V di/dt = 1200A/μs	T _j = 25°C		70		ns
	T _j = 125°C			140			
Q _{rr}	Reverse Recovery Charge			T _j = 25°C		0.6	
			T _j = 125°C		4.2		
R _{thJC}	Junction to Case Thermal Resistance					0.16	°C/W

Parallel diode ratings and characteristics

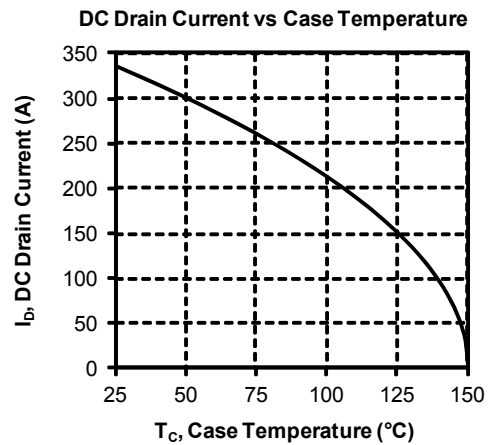
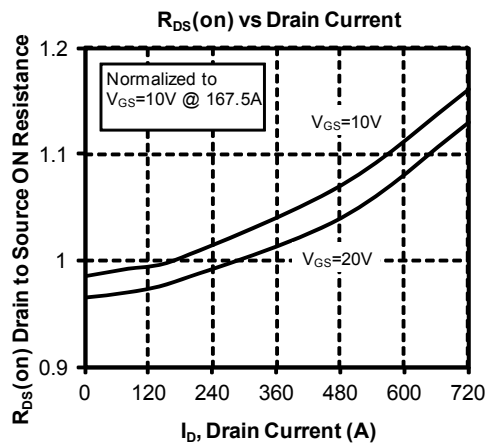
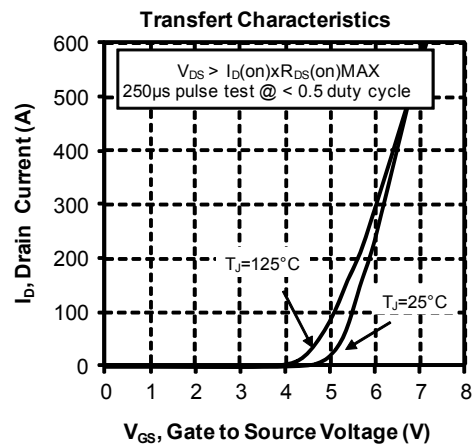
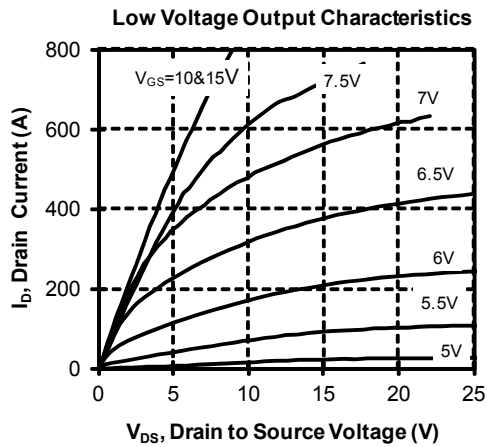
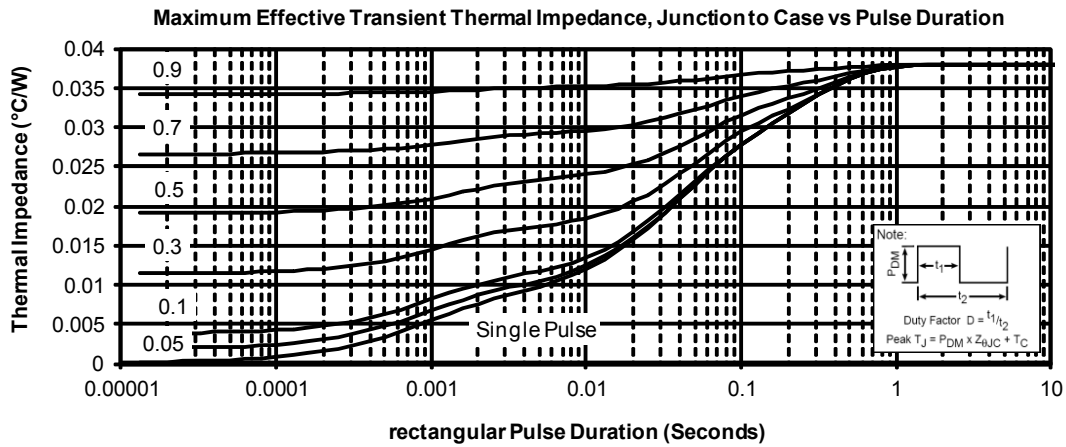
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R = 600V				150	μA
I _F	DC Forward Current		T _c = 80°C		360		A
V _F	Diode Forward Voltage	I _F = 360A			1.7	2.5	V
		I _F = 720A			2		
		I _F = 360A	T _j = 125°C		1.4		
t _{rr}	Reverse Recovery Time	I _F = 360A V _R = 400V di/dt = 1200A/μs	T _j = 25°C		70		ns
			T _j = 125°C		140		
Q _{rr}	Reverse Recovery Charge			T _j = 25°C		0.6	
			T _j = 125°C		4.2		
R _{thJC}	Junction to Case Thermal Resistance					0.16	°C/W

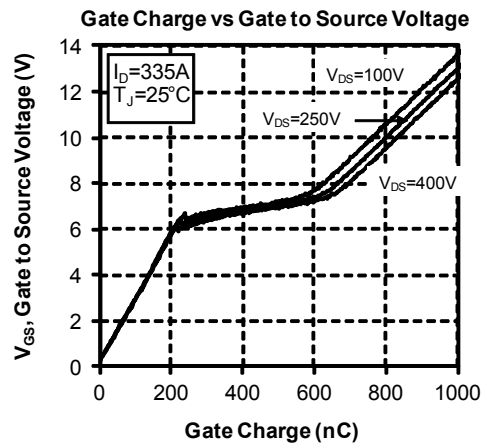
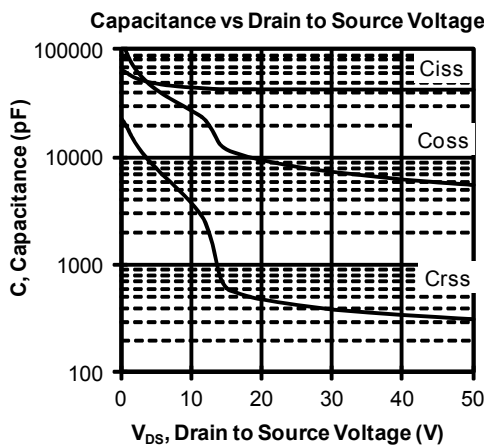
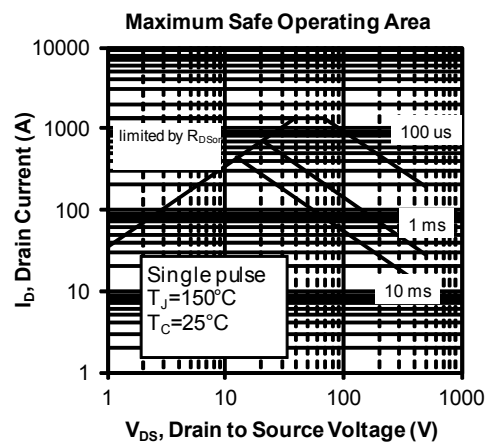
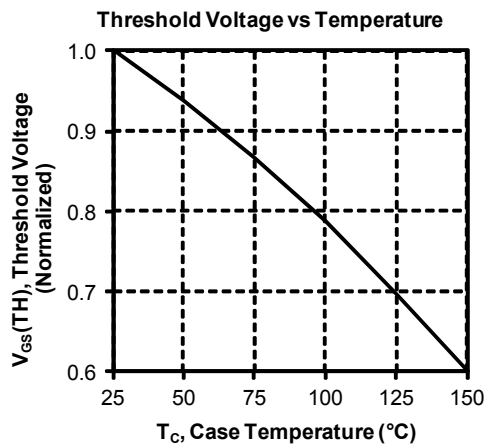
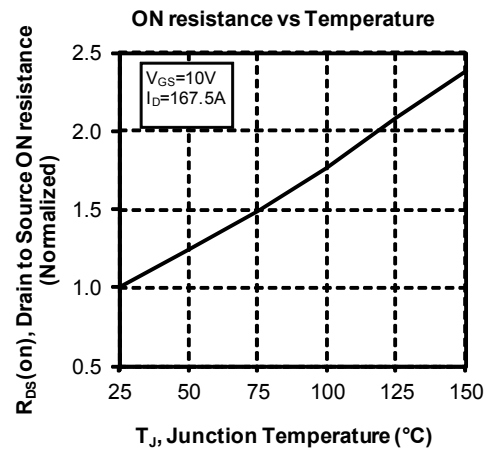
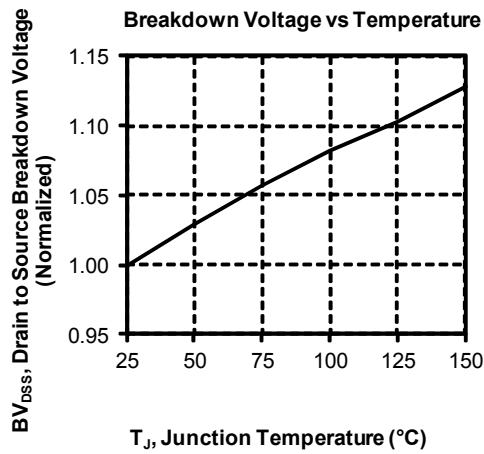
Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T _J	Operating junction temperature range			-40	150	°C
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	
T _{STG}	Storage Temperature Range			-40	125	
T _C	Operating Case Temperature			-40	100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				300	g

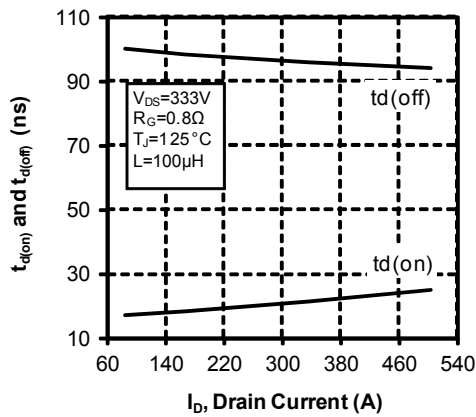
SP6 Package outline (dimensions in mm)

 See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve

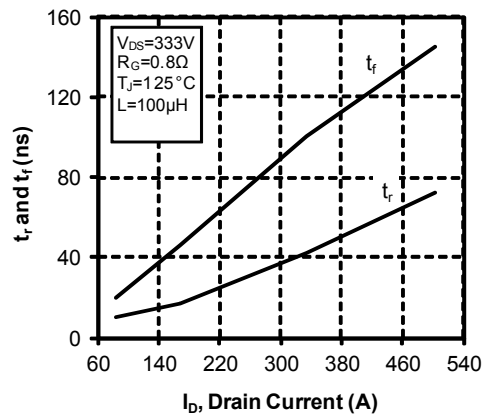




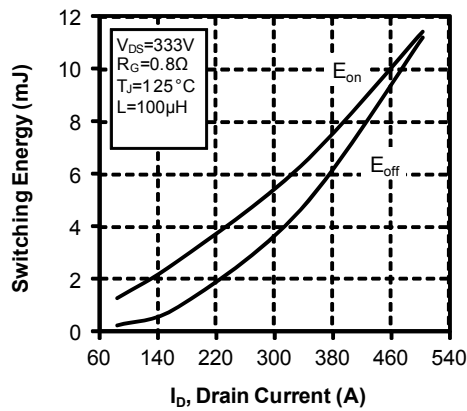
Delay Times vs Current



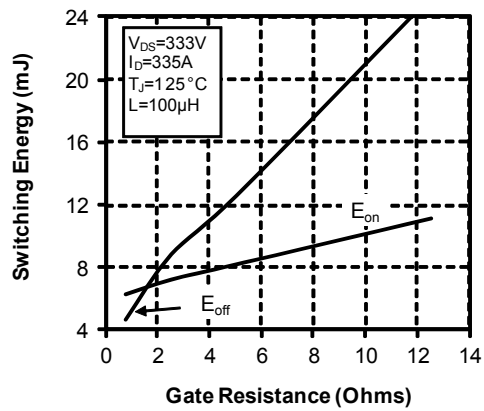
Rise and Fall times vs Current



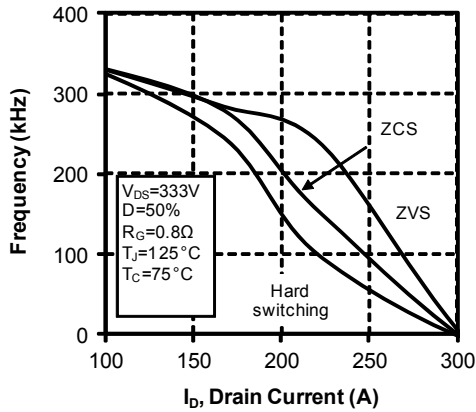
Switching Energy vs Current



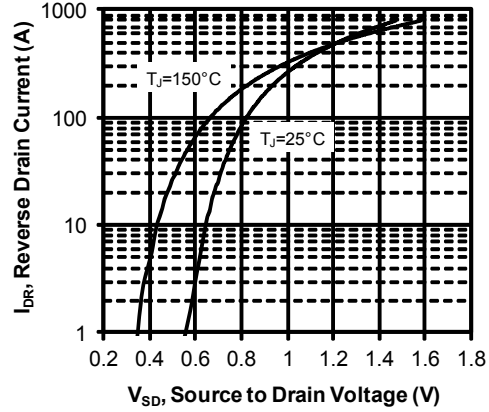
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



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